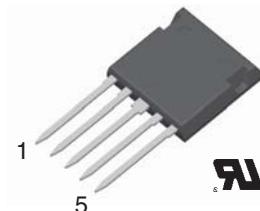
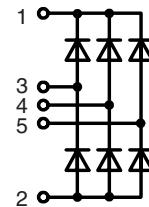


Three Phase Rectifier Bridge

in ISOPLUS i4-PAC™

V_{RRM} = 1600 V
I_{D(AV)M} = 50 A
I_{FSM} = 200 A



Rectifier Bridge

Symbol	Conditions	Maximum Ratings		
V_{RRM}		1600		V
I_{FAV}	T _C = 90°C; sine 180° (per diode)	20		A
I_{D(AV)M}	T _C = 90°C	50		A
I_{FSM}	T _{VJ} = 25°C; t = 10 ms; sine 50 Hz	200		A
P_{tot}	T _C = 25°C (per diode)	60		W

Symbol	Conditions	Characteristic Values		
		(T _{VJ} = 25°C, unless otherwise specified)	min.	typ.
V_F	I _F = 20 A; T _{VJ} = 25°C T _{VJ} = 125°C		1.1 1.1	1.3 V
I_R	V _R = V _{RRM} ; T _{VJ} = 25°C V _R = 0.8•V _{RRM} ; T _{VJ} = 125°C		0.2	10 μA mA
R_{thJC} R_{thJH}	(per diode)		3.2	2.1 K/W K/W

Component

Symbol	Conditions	Maximum Ratings		
T_{VJ}		-55...+150		°C
T_{stg}		-55...+125		°C
V_{ISOL}	I _{ISOL} ≤ 1 mA; 50/60 Hz	2500		V~
F_c	mounting force with clip	20...120		N

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
C_p	coupling capacity between shorted pins and mounting tab in the case	40		pF
d_sd_A	pin - pin	1.7		mm
d_sd_A	pin - backside metal	5.5		mm
Weight		9		g

Data according to IEC 60747 and refer to a single diode unless otherwise stated.

IXYS reserves the right to change limits, test conditions and dimensions.

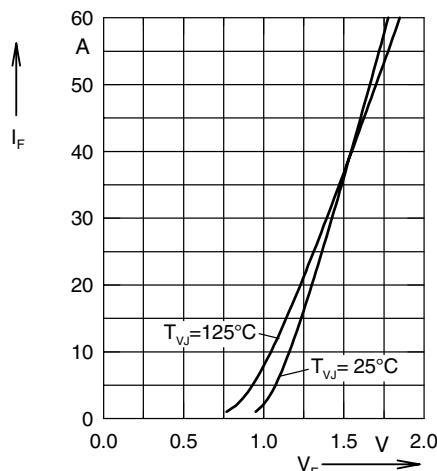


Fig. 1 Forward current vs. voltage drop per leg

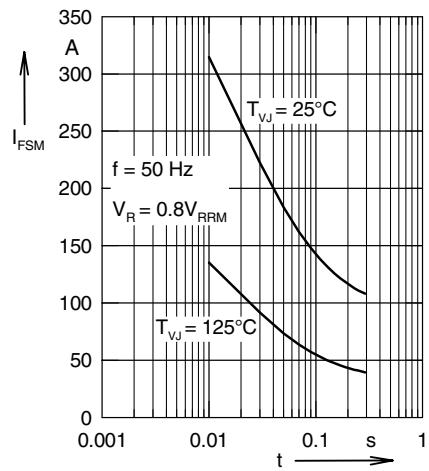


Fig. 2 Surge overload current

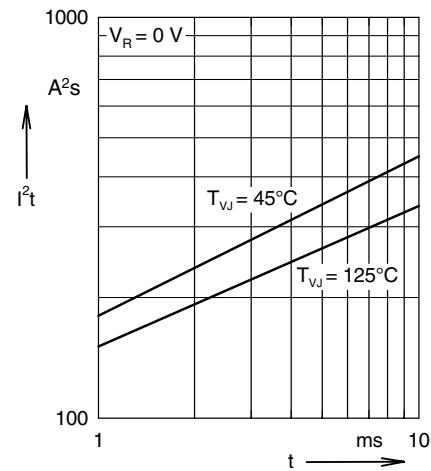
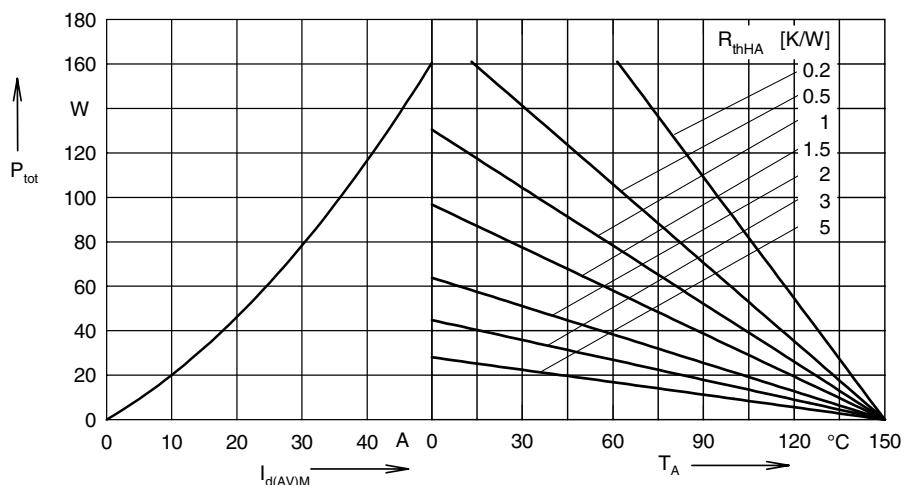
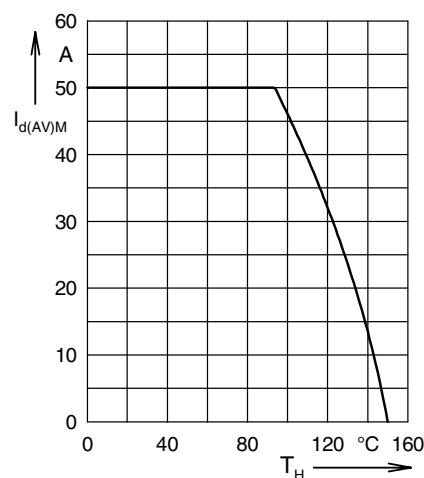
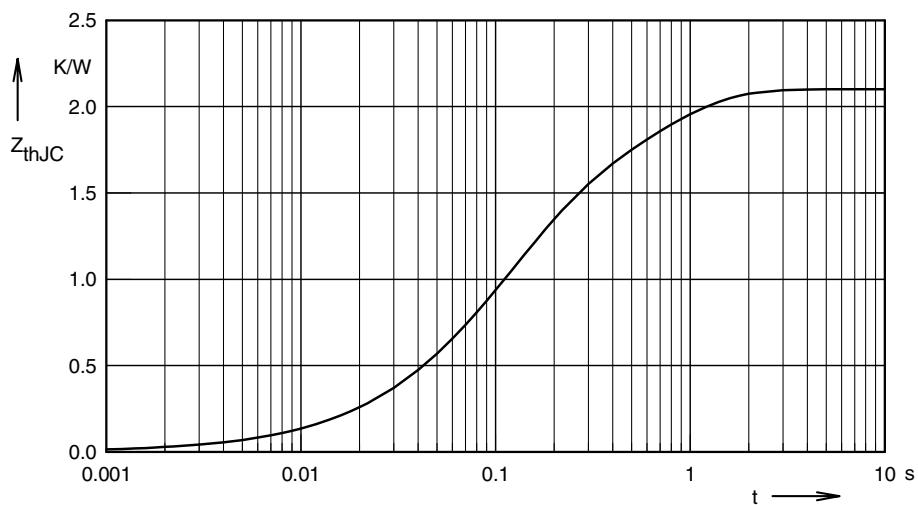
Fig. 3 t versus time per diode

Fig. 4 Power dissipation versus direct output current and ambient temperature; sinusoidal 120°

Fig. 5 Max. forward current vs. case temperature $I_{d(AVM)} = f(T_{case})$ Fig. 6 Transient thermal impedance junction to case Z_{thJC} Constants for Z_{thJC} calculation

i	R_{thi} (K/W)	t_i (s)
1	1.159	0.1015
2	0.1286	0.1026
3	0.2651	0.4919
4	0.5473	0.62